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6. The method of claim 1 wherein the metal is present in an amount of about 50 atomic percent or more.

7. The method of claim 1 wherein the substrate is a semiconductor substrate or substrate assembly.

8. The method of claim 1 wherein the polishing surface comprises a polishing pad and the planarization composition comprises a plurality of abrasive particles.

9. The method of claim 1 which is carried out in one step.

10. The method of claim 1 wherein the halogen-containing compound is selected from the group consisting of a halogen, an interhalogen, a halogen-generating compound, and combinations thereof.

11. The method of claim 10 wherein the halogen-containing compound is selected from the group consisting of  $F_2$ ,  $Cl_2$ ,  $Br_2$ ,  $I_2$ ,  $ClBr$ ,  $IBr$ ,  $ICl$ ,  $BrF$ ,  $ClF$ ,  $ClF_3$ ,  $BrF_3$ ,  $ClF_5$ ,  $IF_5$ ,  $IF_7$ ,  $XeF_2$ ,  $HgF_2$ ,  $SF_4$ , alkyl halides, and complexes of  $X_2$  with organic bases, and combinations thereof.

12. The method of claim 1 wherein the halide salt is an inorganic salt.

13. The method of claim 12 wherein the inorganic halide salt is selected from the group consisting of  $NaI$ ,  $KCl$ ,  $KBr$ ,  $NH_4F$ , and combinations thereof.

14. The method of claim 1 wherein the halide salt is an organic salt.

15. The method of claim 14 wherein the organic salt is selected from the group consisting of  $Et_4NBr$ ,  $Me_3NHCl$ ,  $Me_4NF$ , and combinations thereof.

5 16. The method of claim 1 wherein the halogen-containing compound is present in the planarization composition in an amount of at least about 0.1% by weight and the halide salt is present in the planarization composition in an amount of at least about 0.1% by weight.

17. The method of claim 1 wherein the polishing surface comprises a fixed abrasive article.

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18. A planarization method comprising:  
providing a semiconductor substrate or substrate assembly including at least one region of a platinum-containing surface;  
providing a polishing surface;  
providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface; and  
planarizing the at least one region of platinum-containing surface;  
wherein the planarization composition comprises a halogen-containing compound and a halide salt.

20 19. The method of claim 18 wherein the platinum-containing surface of the substrate comprises platinum in elemental form.

25 20. The method of claim 18 wherein the platinum is present in an amount of about 50 atomic percent or more.

21. The method of claim 18 wherein the semiconductor substrate or substrate assembly is a silicon wafer.

22. The method of claim 18 wherein the polishing surface comprises a polishing pad and the planarization composition comprises a plurality of abrasive particles.

5 23. The method of claim 18 wherein the halogen-containing compound is selected from the group consisting of a halogen, an interhalogen, a halogen-generating compound, and combinations thereof.

10 24. The method of claim 23 wherein the halogen-containing compound is selected from the group consisting of  $F_2$ ,  $Cl_2$ ,  $Br_2$ ,  $I_2$ ,  $ClBr$ ,  $IBr$ ,  $ICl$ ,  $BrF$ ,  $ClF$ ,  $ClF_3$ ,  $BrF_3$ ,  $ClF_5$ ,  $IF_5$ ,  $IF_7$ ,  $XeF_2$ ,  $HgF_2$ ,  $SF_4$ , alkyl halides, and complexes of  $X_2$  with organic bases, and combinations thereof.

15 25. The method of claim 18 wherein the halide salt is an inorganic salt.

26. The method of claim 25 wherein the inorganic halide salt is selected from the group consisting of  $NaI$ ,  $KCl$ ,  $KBr$ ,  $NH_4F$  and combinations thereof.

20 27. The method of claim 18 wherein the halide salt is an organic salt.

28. The method of claim 27 wherein the organic salt is selected from the group consisting of  $Et_4NBr$ ,  $Me_3NHCl$ ,  $Me_4NF$ , and combinations thereof.

25 29. The method of claim 18 wherein the halogen-containing compound is present in the planarization composition in an amount of at least about 0.1% by weight and the halide salt is present in the planarization composition in an amount of at least about 0.1% by weight.

30 30. The method of claim 18 wherein the polishing surface comprises a fixed abrasive article.

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31. A planarization method comprising:
- positioning a metal-containing surface of a substrate to interface with a polishing surface, wherein the metal-containing surface comprises a metal selected from the group consisting of a Group VIIIB metal, a Group IB metal, and a combination thereof;
  - supplying a planarization composition in proximity to the interface;
  - and
  - planarizing the substrate surface;
- wherein the planarization composition comprises:
- a halogen-containing compound selected from the group consisting of  $F_2$ ,  $Cl_2$ ,  $Br_2$ ,  $I_2$ ,  $ClBr$ ,  $IBr$ ,  $ICl$ ,  $BrF$ ,  $ClF$ ,  $ClF_3$ ,  $BrF_3$ ,  $ClF_5$ ,  $IF_5$ ,  $IF_7$ ,  $XeF_2$ ,  $HgF_2$ ,  $SF_4$ , alkyl halides, and complexes of  $X_2$  with organic bases, and combinations thereof; and
  - a halide salt selected from the group consisting of  $NaI$ ,  $KCl$ ,  $KBr$ ,  $NH_4F$ ,  $Et_4NBr$ ,  $Me_3NHCl$ ,  $Me_4NF$ , and combinations thereof.
32. The method of claim 31 wherein the halogen-containing compound is present in the planarization composition in an amount of about 1% to about 10% by weight.
33. The method of claim 31 wherein the halide salt is present in the planarization composition in an amount of about 1% to about 10% by weight.
34. A planarization method comprising:
- providing a semiconductor substrate or substrate assembly including at least one region of a platinum-containing surface;
  - providing a polishing surface;
  - providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface; and

planarizing the at least one region of platinum-containing surface;  
wherein the planarization composition comprises:

a halogen-containing compound selected from the group  
consisting of  $F_2$ ,  $Cl_2$ ,  $Br_2$ ,  $I_2$ ,  $ClBr$ ,  $IBr$ ,  $ICl$ ,  $BrF$ ,  $ClF$ ,  $ClF_3$ ,  $BrF_3$ ,  
5  $ClF_5$ ,  $IF_5$ ,  $IF_7$ ,  $XeF_2$ ,  $HgF_2$ ,  $SF_4$ , alkyl halides, and complexes of  $X_2$   
with organic bases, and combinations thereof; and

a halide salt selected from the group consisting of  $NaI$ ,  $KCl$ ,  
 $KBr$ ,  $NH_4F$ ,  $Et_4NBr$ ,  $Me_3NHCl$ ,  $Me_4NF$ , and combinations thereof.

10 35. The method of claim 34 wherein the halogen-containing compound is present  
in the planarization composition in an amount of about 1% to about 10% by  
weight.

15 36. The method of claim 34 wherein the halide salt is present in the planarization  
composition in an amount of about 1% to about 10% by weight.

20 37. A planarization method for use in forming an interconnect, the method  
comprising:

providing a semiconductor substrate or substrate assembly having a  
patterned dielectric layer formed thereon and a metal-containing layer formed  
over the patterned dielectric layer, wherein the metal-containing layer  
comprises a metal selected from the group consisting of a Group VIIIIB metal,  
a Group IB metal, and a combination thereof;

25 positioning a first portion of a polishing surface for contact with the  
metal-containing layer;

providing a planarization composition in proximity to the contact  
between the polishing surface and the metal-containing layer; and

planarizing the metal-containing layer;

30 wherein the planarization composition comprises a halogen-containing  
compound and a halide salt.

38. The method of claim 37 wherein the polishing surface comprises a polishing pad and the planarization composition comprises a plurality of abrasive particles.

5 39. The method of claim 37 wherein the halogen-containing compound is selected from the group consisting of a halogen, an interhalogen, a halogen-generating compound, and combinations thereof.

10 40. The method of claim 39 wherein the halogen-containing compound is selected from the group consisting of  $F_2$ ,  $Cl_2$ ,  $Br_2$ ,  $I_2$ ,  $ClBr$ ,  $IBr$ ,  $ICl$ ,  $BrF$ ,  $ClF$ ,  $ClF_3$ ,  $BrF_3$ ,  $ClF_5$ ,  $IF_5$ ,  $IF_7$ ,  $XeF_2$ ,  $HgF_2$ ,  $SF_4$ , alkyl halides, and complexes of  $X_2$  with organic bases, and combinations thereof.

15 41. The method of claim 37 wherein the halide salt is an inorganic salt.

42. The method of claim 41 wherein the inorganic halide salt is selected from the group consisting of  $NaI$ ,  $KCl$ ,  $KBr$ ,  $NH_4F$  and combinations thereof.

20 43. The method of claim 37 wherein the halide salt is an organic salt.

44. The method of claim 43 wherein the organic salt is selected from the group consisting of  $Et_4NBr$ ,  $Me_3NHCl$ ,  $Me_4NF$ , and combinations thereof.

25 45. The method of claim 37 wherein the halogen-containing compound is present in the planarization composition in an amount of at least about 0.1% by weight.

30 46. The method of claim 45 wherein the halogen-containing compound is present in the planarization composition in an amount of about 1% to about 10% by weight.

47. The method of claim 37 wherein the halide salt is present in the planarization composition in an amount of at least about 0.1% by weight.

5 48. The method of claim 47 wherein the halide salt is present in the planarization composition in an amount of about 1% to about 10% by weight.

49. The method of claim 37 wherein the polishing surface comprises a fixed abrasive article.

10 50. A planarization method for use in forming an interconnect, the method comprising:

15 providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a metal-containing layer formed over the patterned dielectric layer, wherein the metal-containing layer comprises a metal selected from the group consisting of a Group VIIIB metal, a Group IB metal, and a combination thereof;

20 positioning a first portion of a polishing surface for contact with the metal-containing layer;

25 providing a planarization composition in proximity to the contact between the polishing surface and the metal-containing layer; and

planarizing the metal-containing layer;

wherein the planarization composition comprises:

30 a halogen-containing compound selected from the group consisting of  $F_2$ ,  $Cl_2$ ,  $Br_2$ ,  $I_2$ ,  $ClBr$ ,  $IBr$ ,  $ICl$ ,  $BrF$ ,  $ClF$ ,  $ClF_3$ ,  $BrF_3$ ,  $ClF_5$ ,  $IF_5$ ,  $IF_7$ ,  $XeF_2$ ,  $HgF_2$ ,  $SF_4$ , alkyl halides, and complexes of  $X_2$  with organic bases, and combinations thereof; and

a halide salt selected from the group consisting of  $NaI$ ,  $KCl$ ,  $KBr$ ,  $NH_4F$ ,  $Et_4NBr$ ,  $Me_3NHCl$ ,  $Me_4NF$ , and combinations thereof.